### AM4992N

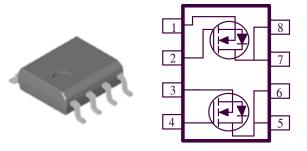
## **Analog Power**

# Dual N-Channel 100-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)} m(\Omega)$	I <sub>D</sub> (A)	
100	430 @ $V_{GS} = 10V$	1.8	
	$480 @ V_{GS} = 4.5V$	1.7	



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C UNLESS OTHERWISE NOTED)					
Parameter			Limit	Units	
Drain-Source Voltage		V <sub>DS</sub>	100	v	
Gate-Source Voltage		V <sub>GS</sub>	±20	v	
Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}C$	T_	1.8		
Continuous Drain Current	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	ID	1.4	А	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	±7		
Continuous Source Current (Diode Conduction) <sup>a</sup>			1.3	Α	
	$T_A=25^{\circ}C$	D	2.1	W	
Power Dissipation <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	гD	1.3		
Operating Junction and Storage Temperature Range		TJ, Tstg	-55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Maximum	Units		
Maximum Junction-to-Case <sup>a</sup>	t <= 5 sec	$R_{\theta JC}$	40	°C/W		
Maximum Junction-to-Ambient <sup>a</sup>	t <= 5 sec	$R_{\theta JA}$	60	°C/W		

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

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			Limits			<b>T</b> T •4	
<b>Parameter</b>	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Drain-Source Breakdown Voltage	V(BR)DSS	$V_{\rm GS} = 0 \text{ V}, \text{ I}_{\rm D} = 250 \text{ uA}$				v	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			Ň	
Gate-Body Leakage	Igss	$V_{DS} = 0 V, V_{GS} = 20 V$			±100	nA	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate voltage Drain Current	IDSS	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA	
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10 V$	3			Α	
Drain-Source On-Resistance <sup>A</sup>	ĨDS(on)	$V_{GS} = 10 \text{ V}, I_D = 1.8 \text{ A}$			430		
		$V_{GS} = 4.5 \text{ V}, I_D = 1.7 \text{ A}$			480	mΩ	
Forward Tranconductance <sup>A</sup>	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_D = 1.8 \text{ A}$		3.6		S	
Diode Forward Voltage	V <sub>SD</sub>	$I_S = 2.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.7		V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg	$V_{DS} = 15 V, V_{GS} = 5 V,$		3		nC	
Gate-Source Charge	Qgs	$v_{DS} = 15 v$ , $v_{GS} = 5 v$ , ID = 1.8 A		1.5			
Gate-Drain Charge	Qgd	ID = 1.8  A		2.2			
Switching					•	•	
Turn-On Delay Time	t <sub>d(on)</sub>			4.8		nS	
Rise Time	tr	$V_{DD}$ = 25 V, $R_L$ = 25 $\Omega$ , $\mathrm{ID}$ = 1 A,		3.9			
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 V$		12.7			
Fall-Time	tf	1		3.2			

Notes

- a. Pulse test:  $PW \le 300$  us duty cycle  $\le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

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